

# **GENERAL DESCRIPTION**

DP8205 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

# **PRODUCT SUMMARY**

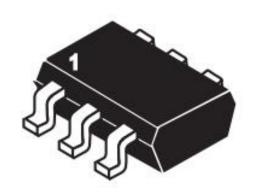
 $V_{DS}$  20 V

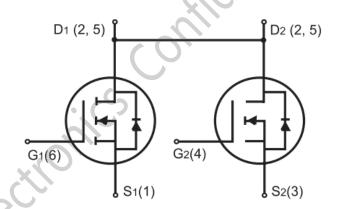
 $I_D$  (at  $V_{GS}$ =4.5V) 5.0A

 $R_{DS(ON)}$  (at  $V_{GS} = 4.5V$ ) < 29m $\Omega$ 

 $R_{DS(ON)}$  (at  $V_{GS} = 2.5V$ ) < 34m $\Omega$ 

#### SOT23-6





<b>Absolute Maximum</b>	Ratings	T∆=25°C ı	inless o	therwise noted
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Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±12	V
Drain Current-Continuous @ T <sub>J</sub> =25°C	I <sub>D</sub>	5	Α
Pulsed <sup>b</sup>	I <sub>DM</sub>	20	Α
Drain-Sourse Diode Forward Current <sup>a</sup>	I <sub>S</sub>	2.5	Α
Maximum Power Dissipation <sup>a</sup>	$P_{D}$	1.25	W
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	°C

#### **Thermal Characteristic**

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>OJA</sub>	100	°C/W



# **ELECTRICAL CHARACTERISTICS** (TA=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Турс	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	-	-	<b>V</b>	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}=20V,V_{GS}=0V$	-	-	1	μΑ	
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	±100	nA	
On Characteristics							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	0.5	0.7	1.2	V	
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A	14	20	29	mΩ	
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.5A	17	27	34	mΩ	
Forward Transconductance	g <sub>FS</sub>	$V_{DS}=5V,I_{D}=7A$	-	17.7	-	S	
Dynamic Characteristics							
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =8V,	-	802	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V,	_	153	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	122	-	pF	
Switching Characteristics							
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V,	-	18	-	nS	
Turn-on Rise Time	t <sub>i</sub>	I <sub>D</sub> =1A	-	5	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =4.5V, $R_{GEN}$ =10 $\Omega$ ,	-	43.8	-	nS	
Turn-Off Fall Time	t <sub>f</sub>	$R_L=10\Omega$	-	20	-	nS	
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V,	-	10.5	-	nC	
Gate-Source Charge	$Q_{gs}$	I <sub>D</sub> =4A,	_	2	-	nC	
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V	-	2.5	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =1.7A	-	-	1.2	V	

## **Notes:**

- a. Surface Mounted on FR4 Board ,T<10 sec;
- b. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- c. Guaranteed by Design, not subject to production testing.



# TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

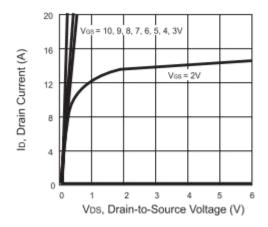


Figure 1. Output Characteristics

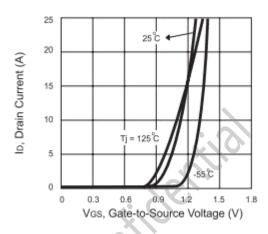


Figure 2. Thansfer Characteristics

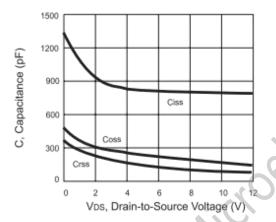


Figure 3. Capacitance

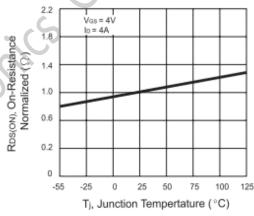


Figure 4. On-Resistance Variation with Temperature

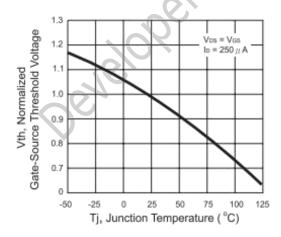


Figure 5. Gate Threshold Variation with Temperature

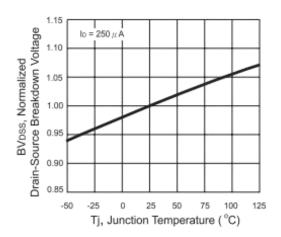


Figure 6. Breakdown Voltage Variation with Temperature



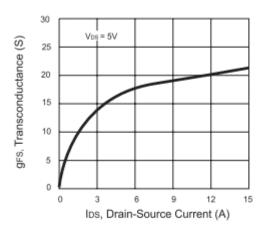


Figure 7. Transconductance Variation with Drain Current

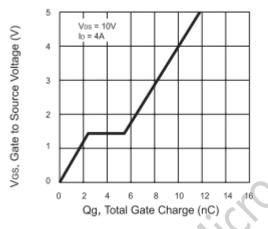


Figure 9. Gate Charge

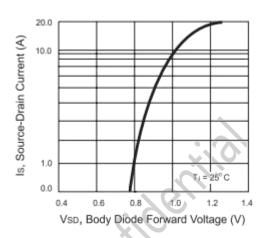


Figure 8. Body Diode Forward Voltage
Variation with Source Current

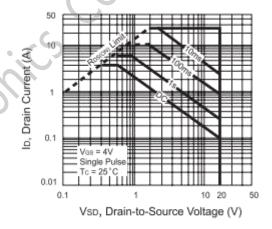


Figure 10. Maximum Safe Operating Area

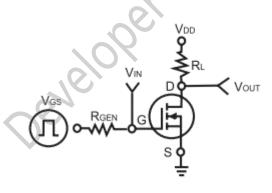


Figure 11. Switching Test Circuit

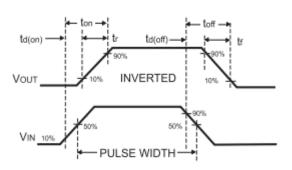


Figure 12. Switching Waveforms



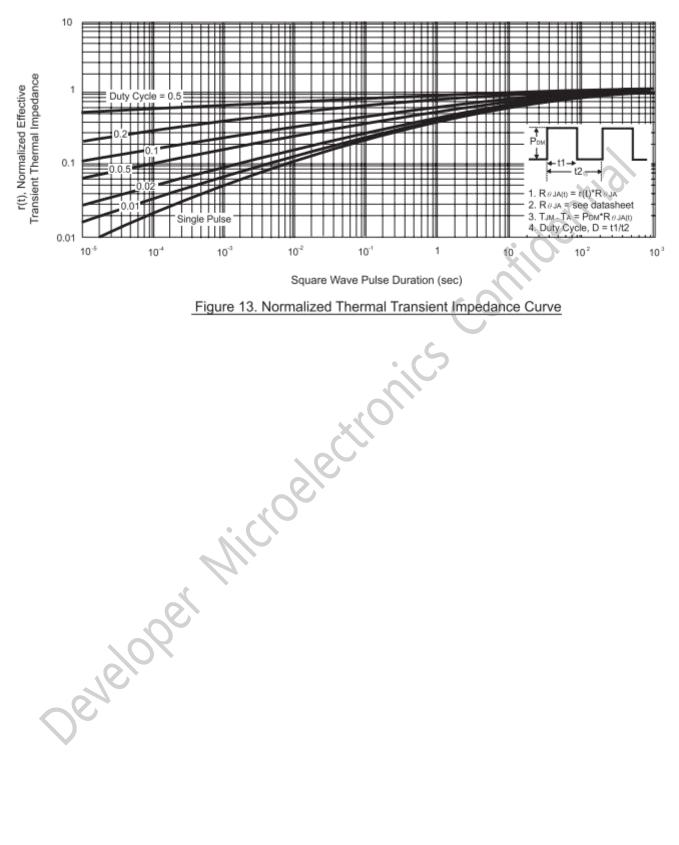
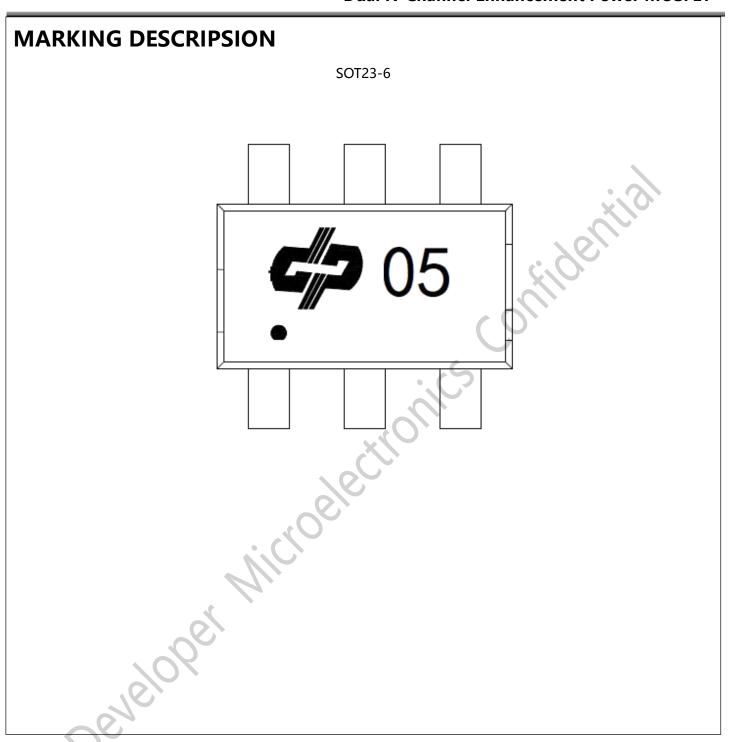


Figure 13. Normalized Thermal Transient Impedance Curve



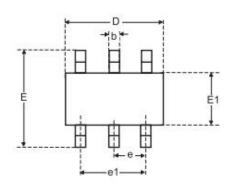


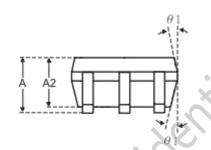


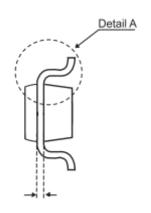


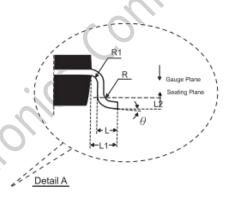
# **PACKAGE OUTLINE DIMENSIONS**

SOT23-6



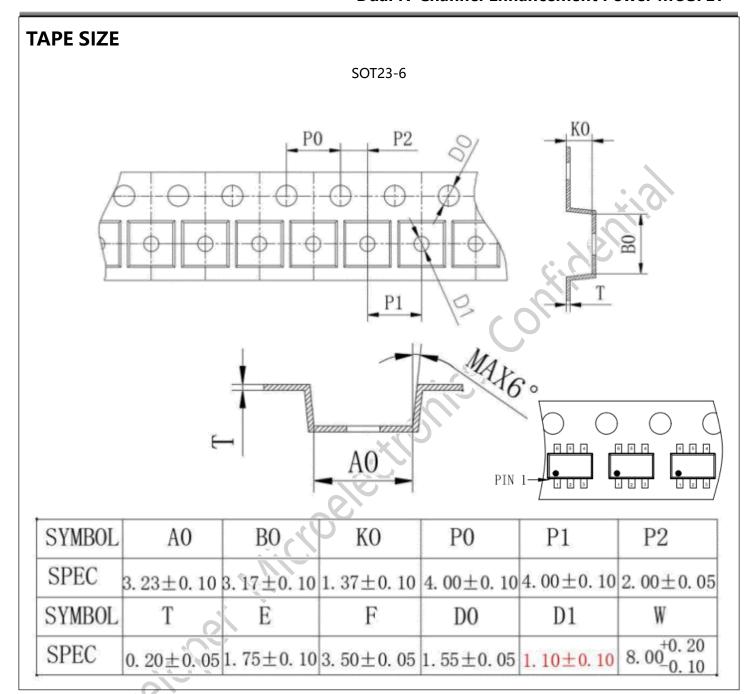






	SYMBOLS	MILLIMETERS			
		Min.	Nom.	Max.	
	A	· -	-	1.45	
18/0/8	A2	0.90	0.15	1.30	
	b	0.30	-	0.50	
	С	0.08	_	0.22	
	D	2.70	2.90	3.10	
	Е	2.50	2.80	3.10	
	E1	1.50	1.60	1.70	
	е	0.95 BSC			
0/1	e1	1.90 BSC			
	L	0.30	0.45	0.60	
	L1	0.60 BSC			
	L2	0.20 BSC			
	R	0.10	-	-	
	R1	0.10	-	0.25	
	θ	0°	4 °	8°	
	θ1	0°	10°	15°	







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